

## 9.3 Summary

### 9.3.1 Summary to: 9. Optoelectronics

Optoelectronics has *two* basic branches:

1. Light in  $\Rightarrow$  electrical signal out:
  - **Optical sensors** as single elements
  - "**CCD**" chips in "megapixel" matrices.
2. Electricity in  $\Rightarrow$  light out; in two paradigmatic versions:
  - **LED's**
  - **Laser** diodes

Here we only look at the second branch.

- The semiconductors of choice are mostly the **III-V's**, usually in single-crystalline perfect thin films.
- The present day (**2008**) range of wavelength covers the **IR** to near **UV**.
- Indirect semiconductors like **GaP** can be used too, if some "tricks" are used.

The **index of refraction**  $n=(\epsilon)^{1/2}$  and thus the dielectric constant  $\epsilon$  become important

- Semiconductors have a relatively large index of refraction at photon energies below the bandgap of  $n \approx 3 - 4$ .
- Diamond has the highest  $n$  in the visible region

The **thermal conductivity** becomes important because for generating light one needs **power** (which we avoided as much as possible for signal processing with **Si!**)

- Again, diamond has the highest thermal conductivity of all known materials - **5** times better than **Cu!**

**LED's** come as cheap little "indicator" lights and recently also as replacement for "light bulbs".

- Intense white light from **LED's** becomes possible, Advantages: High efficiencies and long life time
- The key was the "taming" of the **GaN** material system for blue and **UV LED's**.

**LED's** based on organic semiconductors (**OLED**) are rapidly appearing in **OLED** based displays.

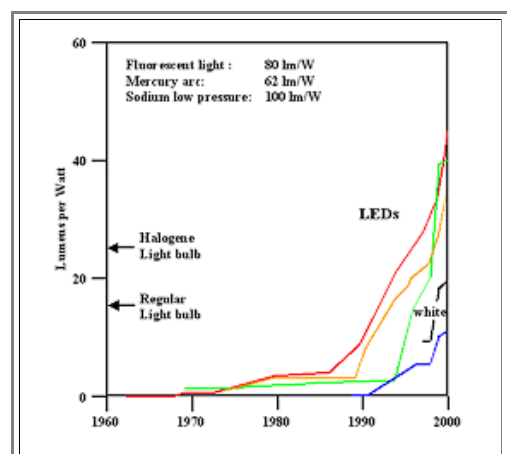
- **Advantage:** High efficiencies because of active light generation.
- **Problem:** Product life time; sensitivity to air.

Semiconductor "Diode" **Lasers** are high-power" **LED's** plus "mirrors"

- **Advantage:** Small and cheap.
- **Problems:** Low power, "Quality".

|                     | Wavelength (nm) | Typical Semiconductor             |
|---------------------|-----------------|-----------------------------------|
| Infrared            | 880             | GaAlAs/GaAs                       |
| Red                 | 660 - 633       | GaAlAs/GaAs                       |
| Orange to Yellow    | 612 - 585       | AlGaInP<br>GaAsP/GaP<br>GaAsP/GaP |
| Green               | 555             | GaP                               |
| Blue to Ultraviolet | 470 - 395       | GaN/SiC<br>GaN/SiC<br>InGaN/SiC   |

| Typical Semiconductor | Dielectric constant | Thermal conductivity [W/cm · K] |
|-----------------------|---------------------|---------------------------------|
| Si                    | 11.9                | 1.5                             |
| GaAs                  | 13.1                | 0,45                            |
| GaP                   | 11.1                | 1.1                             |
| GaN                   | 8.9                 | 1.3                             |
| SiC                   | 10                  | 5                               |
| C (Diamond)           | 5.8                 | 22                              |

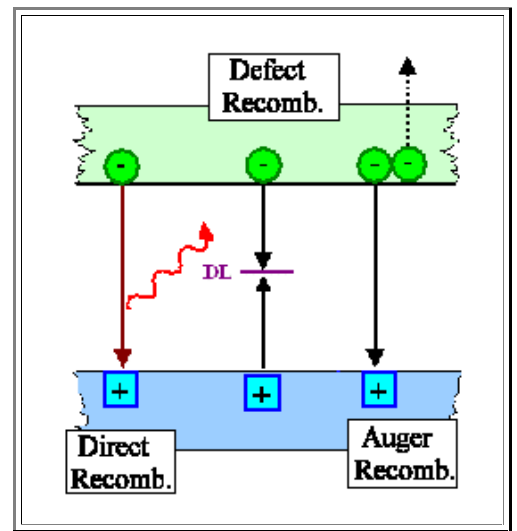


Enabling technology for  
CD / DVD / Blue ray / ...  
memory technologies!

There are always several recombination channels active in parallel

- Direct **band-band recombination**; *producing light*.
- **Defect recombination**; *not* producing light.
- **Auger recombination**; *not* producing light.
- "Exotic" mechanisms like **exciton recombination**; producing light in *indirect* semiconductors like GaP

High efficiency LED's need optimized recombination.

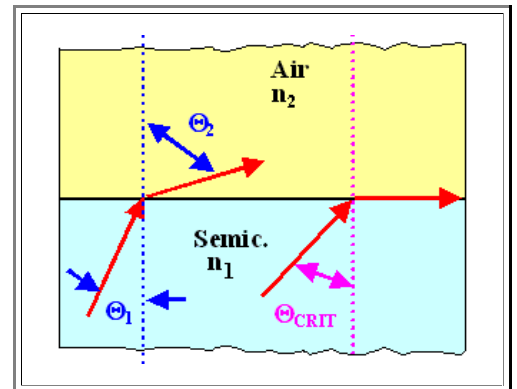


Without "tricks" only a fraction of the light produced gets out of the semiconductor

- Index grating is essential
- Avoiding re-absorption is essential
- Defined recombination volumes are important

Hetero junctions of the **NnP** or **NpP** type are the solution, but create problems of their own

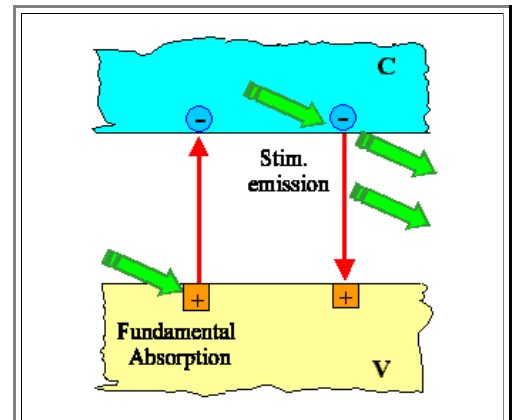
- Hetero-interfaces must be defect free  $\Rightarrow$  Avoid misfit dislocations!



**Laser diodes** are similar to LED's but need to meet two additional conditions

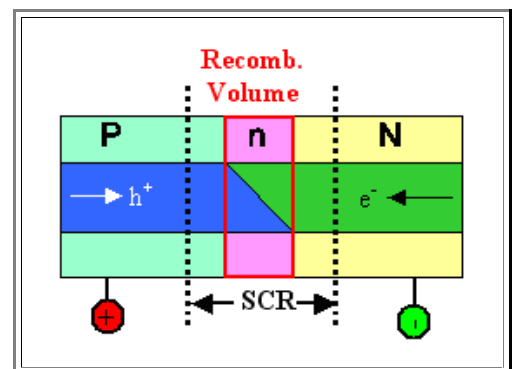
1. The rate of **Stimulated emission**, a new process predicted by A. Einstein concerning the interaction of light and electrons in the conduction band, must be at least as large as the rate of **fundamental absorption**

- **Stimulated emission** results in *two fully coherent* photons for *one* incoming photon and thus allows optical *amplification*.
- Strong stimulated emission his requires large non-equilibrium electron concentrations in the conduction band.  $\Rightarrow$  strong "pumping" is necessary, moving electrons up to the conduction band just as fast as they disappear by recombination.
- In semiconductor junctions pumping can be "easily" achieved by very large injection currents across a forwardly biased (hetero) junction.  $\Rightarrow$  cooling problem!



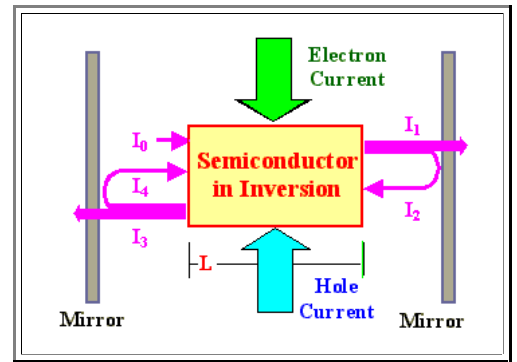
2. There must be some feed-back that turns an (optical) amplifier into an oscillator for one frequency

- **Feed-back** is achieved by partially transparent mirrors.



- Monochromatic output is achieved by the optical resonator formed by two exactly plan-parallel mirrors
- Only wavelengths  $\lambda=2L/i$  ( $i$ =integer) that "fit" into the cavity will be able to exist. Together with the condition  $h\nu=hc/\lambda=E_g$  the Laser wavelength is given

▀ Semiconductor Lasers now span the range from **IR** to **UV**; essential materials are all **III-V's**, in particular the **GaN** family.



▀ **Molecular beam epitaxy** is the deposition method of choice for epitaxial multilayer structures

### Exercise 9.3-1

All Quick Questions to 9.